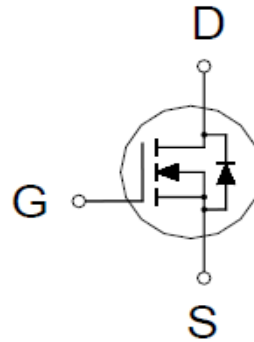
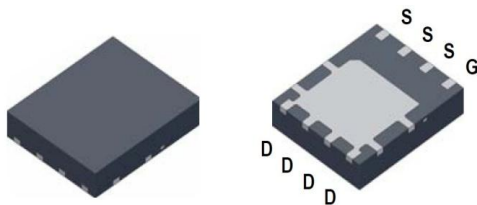


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PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	3.4mΩ @ $V_{GS} = 10V$	75A



PDFN 5X6P

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current ³	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	75	A
	$T_C = 100\text{ }^{\circ}\text{C}$		47	
Pulsed Drain Current ¹		I_{DM}	150	
Continuous Drain Current	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	19.8	
	$T_A = 70\text{ }^{\circ}\text{C}$		15.8	
Avalanche Current		I_{AS}	37	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	71	mJ
Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	35	W
	$T_C = 100\text{ }^{\circ}\text{C}$		14	
Power Dissipation	$T_A = 25\text{ }^{\circ}\text{C}$	P_D	2.4	W
	$T_A = 70\text{ }^{\circ}\text{C}$		1.5	
Operating Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$R_{\theta JA}$		52	$^{\circ}\text{C} / \text{W}$
Junction-to-Case	$R_{\theta JC}$		3.6	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^{\circ}\text{C}$.

³Package limitation current is 26A.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.35	1.75	2.35	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	μA
		V _{DS} = 20V, V _{GS} = 0V, T _J = 55 °C			10	
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 4.5V, I _D = 15A		3.3	5.2	mΩ
		V _{GS} = 10V , I _D = 18A		2.6	3.4	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 18A		60		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		2071		pF
Output Capacitance	C _{oss}			329		
Reverse Transfer Capacitance	C _{rss}			225		
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		1.9		Ω
Total Gate Charge ²	Q _g	V _{GS} =10V		40.9		nC
		V _{GS} =4.5V		21.2		
Gate-Source Charge ²	Q _{gs}	V _{DS} = 15V, I _D = 18A		6.3		
Gate-Drain Charge ²	Q _{gd}			9.6		
Turn-On Delay Time ²	t _{d(on)}	V _{DS} = 15V, I _D ≅ 18A, V _{GS} = 10V, R _{GEN} = 6Ω		26		nS
Rise Time ²	t _r			12		
Turn-Off Delay Time ²	t _{d(off)}			50		
Fall Time ²	t _f			10		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _J = 25 °C)						
Continuous Current ³	I _S				35	A
Forward Voltage ¹	V _{SD}	I _F = 18A, V _{GS} = 0V			1	V
Reverse Recovery Time	t _{rr}	I _F = 18A, dI _F /dt = 100A / μS		25		nS
Reverse Recovery Charge	Q _{rr}			12		nC

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

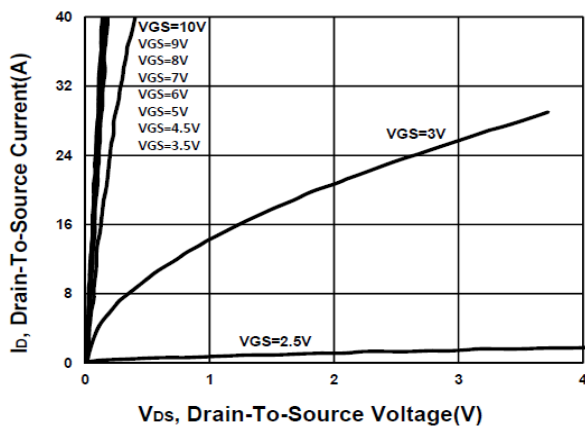
²Independent of operating temperature.

³Package limitation current is 26A.

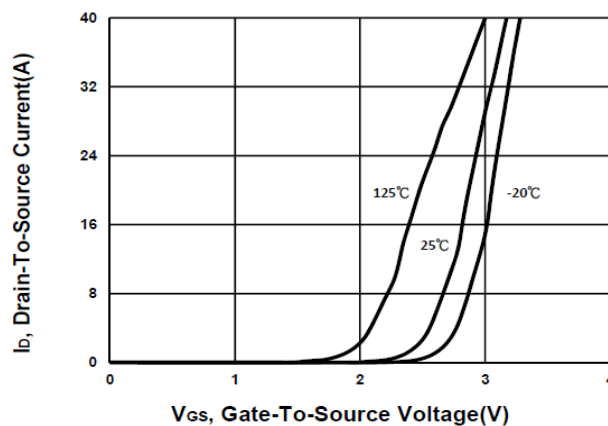
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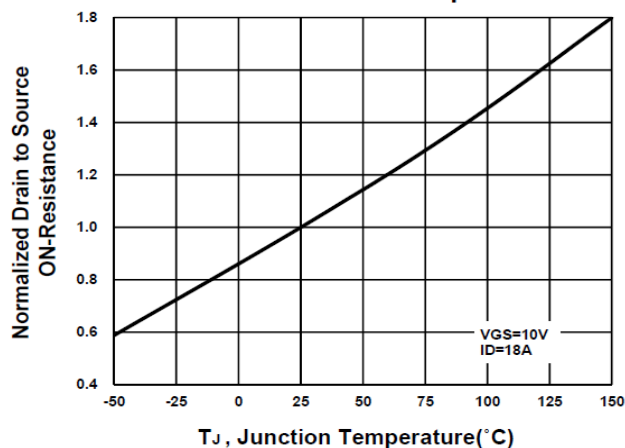
Output Characteristics



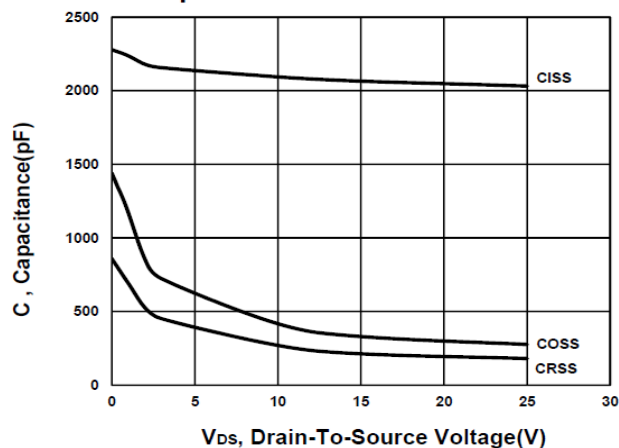
Transfer Characteristics



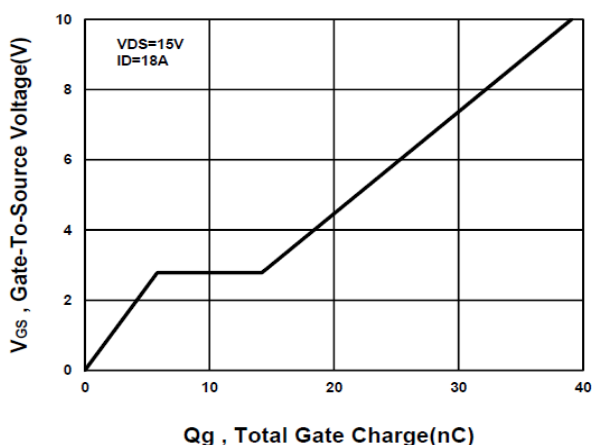
On-Resistance VS Temperature



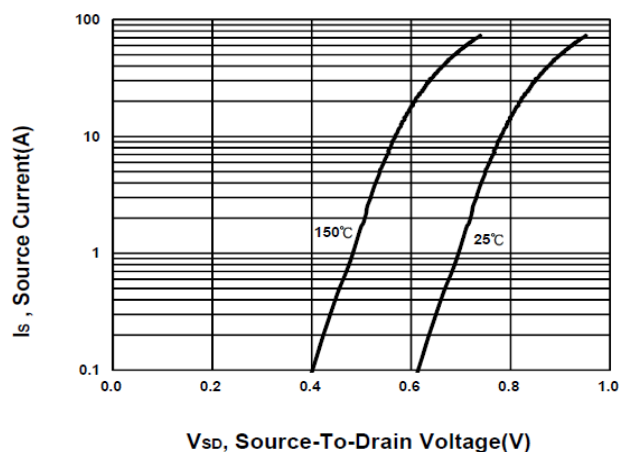
Capacitance Characteristic



Gate charge Characteristics



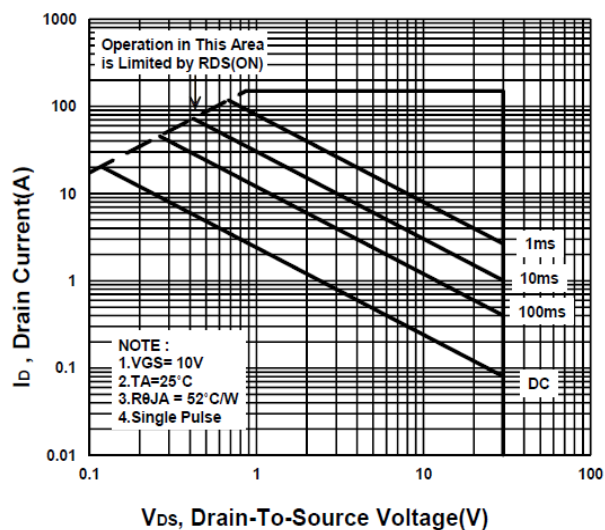
Source-Drain Diode Forward Voltage



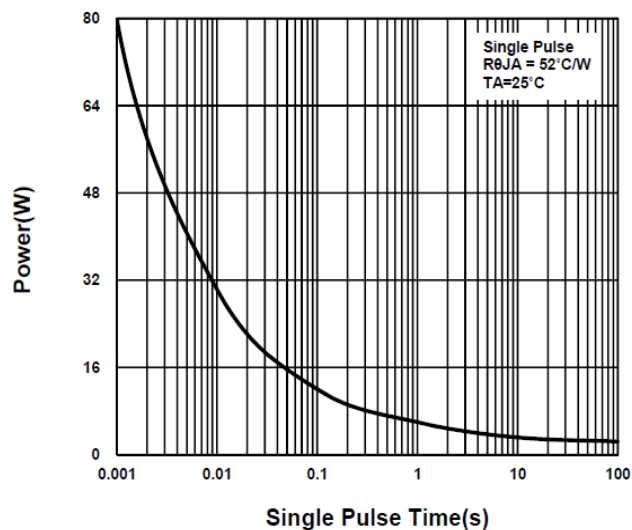
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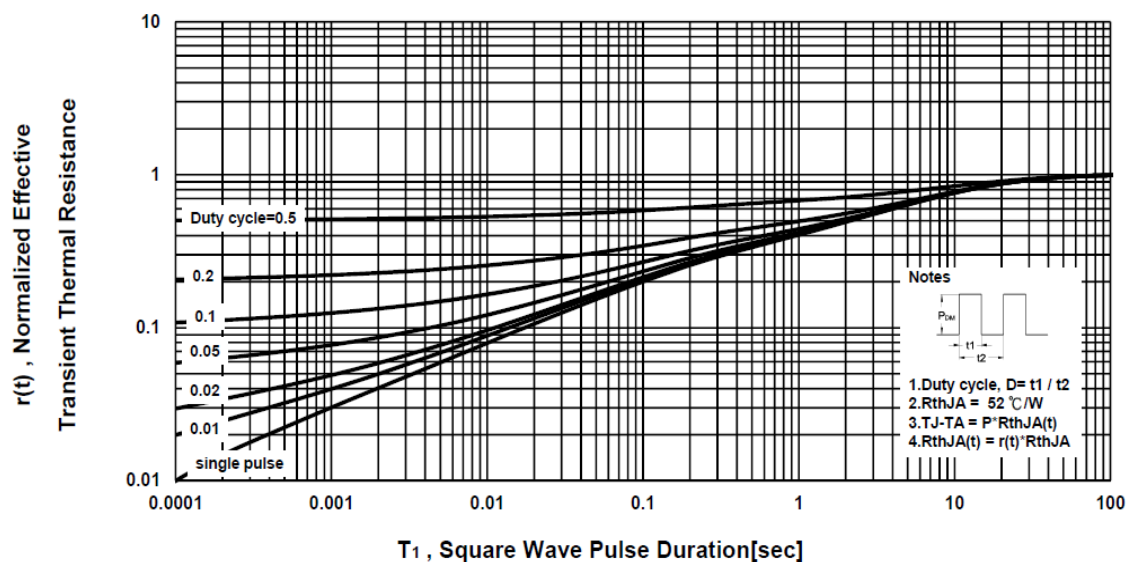
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



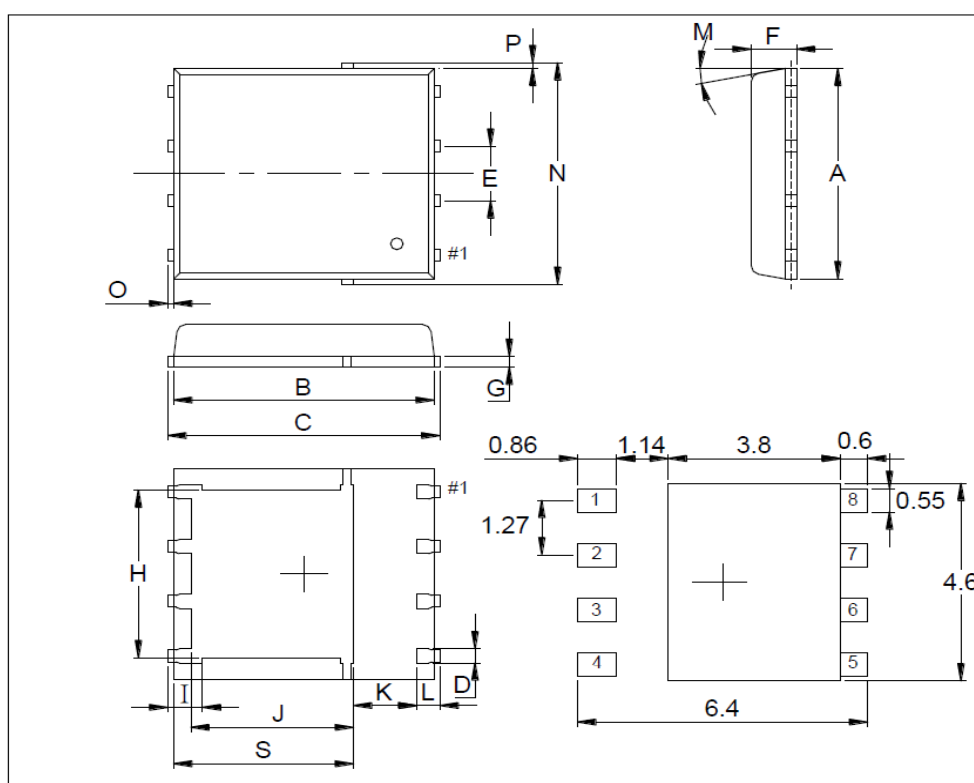
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Package Dimension

PDFN 5x6P MECHANICAL DATA

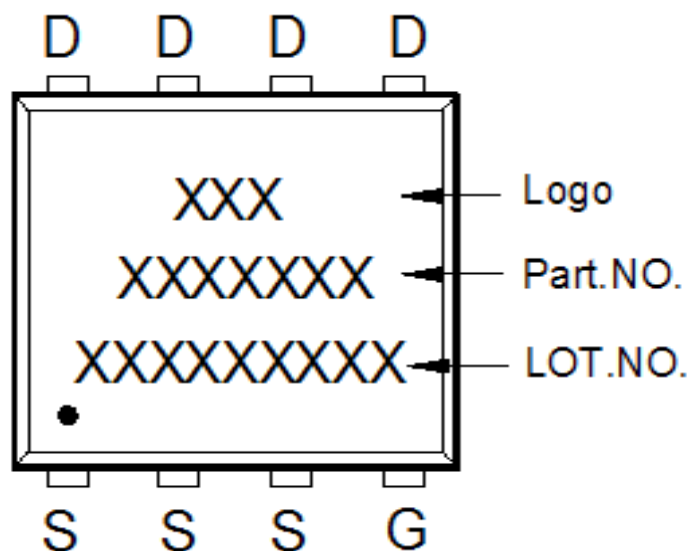
Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8		5.15	J	3.34		3.9
B	5.42		5.9	K	0.9		
C	5.9		6.35	L	0.38		0.711
D	0.3		0.51	M	0°		12°
E	1.17	1.27	1.37	N	4.8		5.4
F	0.8	1	1.2	O	0.05		0.36
G	0.15		0.35	P	0.05		0.25
H	3.67		4.31	S	3.73		4.19
I	0.38		0.71				



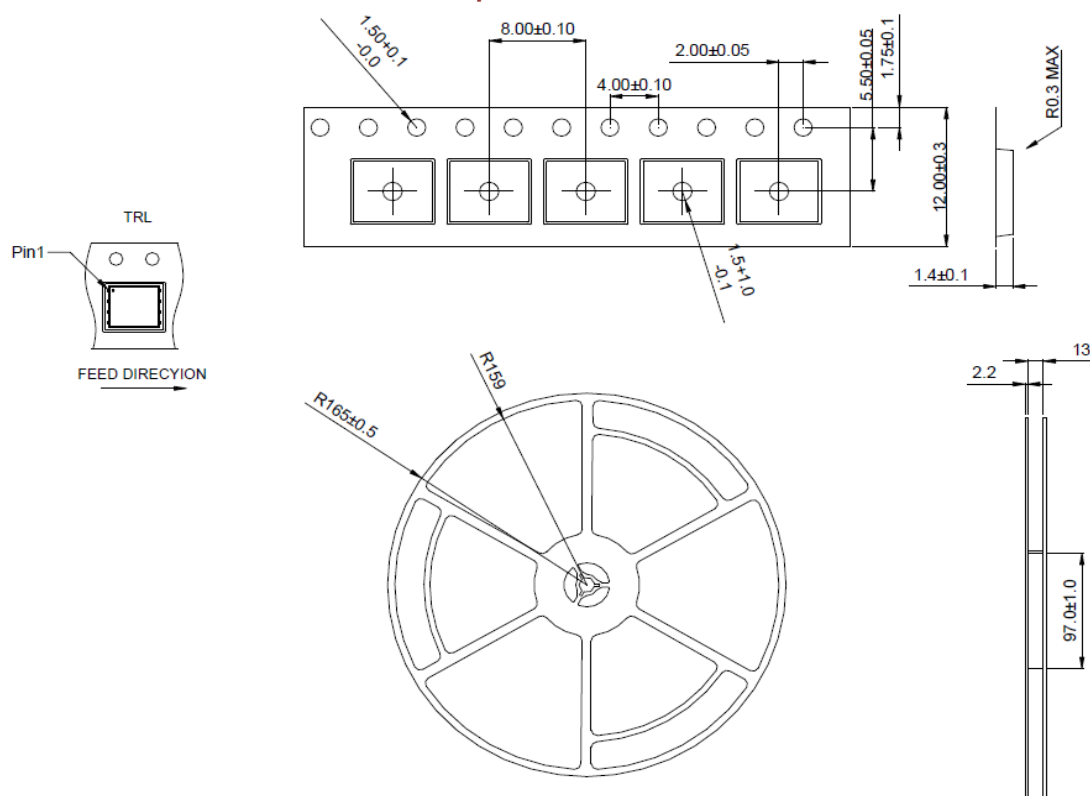
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A. Marking Information



B. Tape&Reel Information:3000pcs/Reel

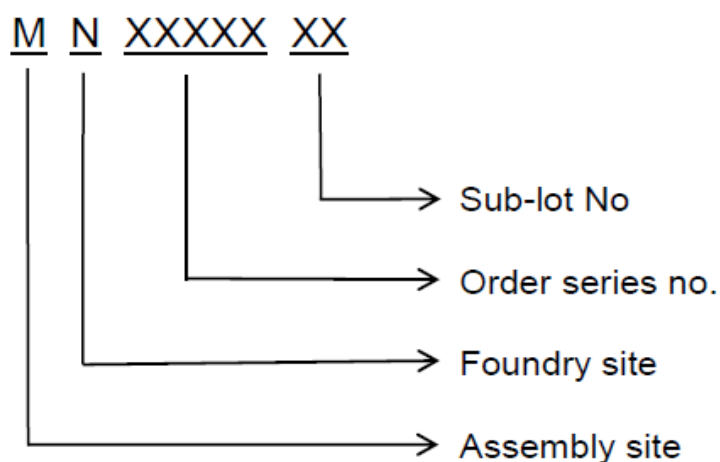


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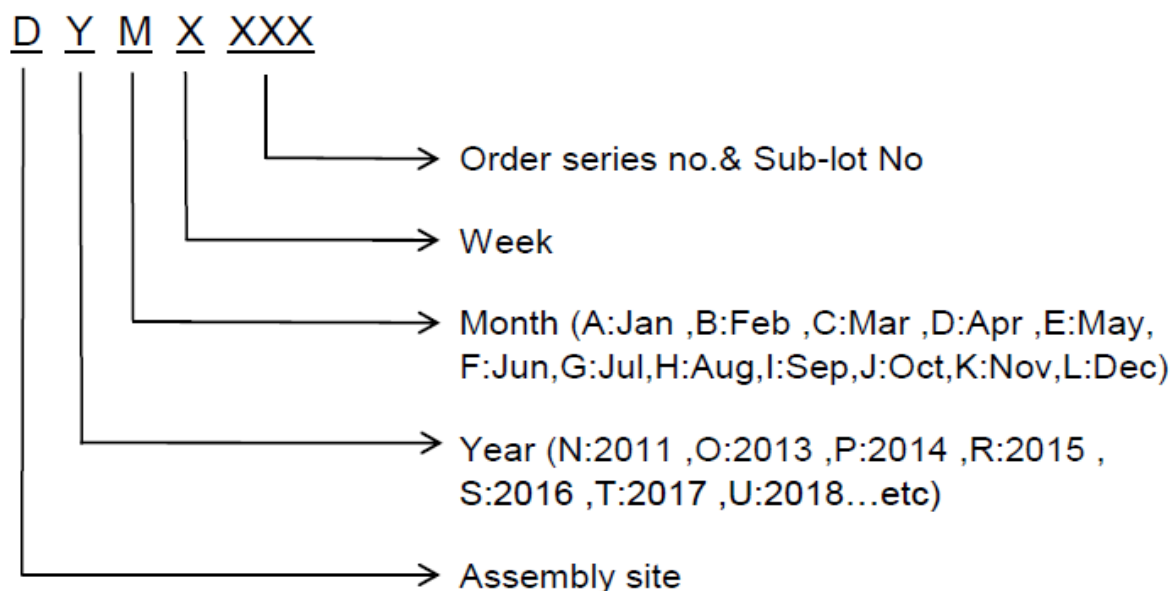
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C. Lot No.&Date Code rule

1.Lot No.



2.Date Code



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D.Label rule

标签内容(Label content)



1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial (或可区分英文"0"和数字"0", "G"和"Q"的字型即可)
3	U-NIKC	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	RoHS label	 long axis: 12 mm minor axis: 6 mm bottom color: White Font color: Black Font style: Arial
11	Halogen Free label	 Diameter: 10 mm bottom color: Green Font color: Black Font style: Arial
12	Scan information	Device / Lot / D/C / QTY, Insert " / " between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least